

FOR USE BY ELECTRICIANS OVERSEAS:

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型 名	社 名	用 途	構 造	最大 定 格 ($T_a=25^{\circ}\text{C}$)					電 気 的 特 性 ($T_a=25^{\circ}\text{C}$)											外 形	備 考		
				V_{CBO} (V)	V_{EBO} (V)	I_C (mA)	P_C (mW)	T_j ($^{\circ}\text{C}$)	I_{CBO} 最大値		直流又はパルス h_{FE}		バイアス		h_{FE} h_{FE}^*	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)			C_{ob} (pF)	$r_{bb'}$ $r_{bb'}^*$ (Ω)
									μA	$V_{CE}(\text{V})$	$I_C(\text{mA})$	$V_{CE}(\text{V})$	$I_C(\text{mA})$										
1	2	3	4	5					6		7		8		9		10	11	12				

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cso} MAXIMUM VALUE AND V_{ce} VALUE (CRITERIA FOR MEASURING I_{cso})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{ce} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{ce} , I_c (CRITERIA FOR MEASURING h PARAMETERS)

* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.

- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ: COMPLEMENTARY TO

型 名	社 名	用 途	構 造	最 大 定 格 (T _a = 25℃)					電 気 的 特 性 (T _a = 25℃)												外 形	備 考	
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (℃)	I _{CB0} 最大値		直流又はパルス h _{FE}		バ イ ア ス		h _{fe} h _{ib} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μU)	f _{βb} f _T * (Mc)	C _{ob} (pF)			r _{bb'} h _{ie} (real)* (Ω)
									(μA)	V _{CB} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)										
2SD897	日 立	SW	Si.T	1500	6	1.5A	50W (T _c =25℃)	150	I _{CS} 500	1500	8	5	300		t _f < 1.2μS							102	水平偏向用
" 898	"	"	"	1500	6	3 A	50W (T _c =25℃)	150	I _{CS} 500	1500					t _f < 1μS							102	水平偏向用
" 899	"	"	"	1500	6	4 A	50W (T _c =25℃)	150	I _{CS} 500	1500					t _f < 1.2μS							102	水平偏向用
" 900	"	"	"	1500	6	5 A	50W (T _c =25℃)	150	I _{CS} 500	1500					t _f < 1.5μS							102	水平偏向用
" 901	日 電	PA	"	230	5	2 A	25W (T _c =25℃)	150	50	150	100	10	400									268	
" 902	三 洋	"	Si.TP	350	5	4 A	80W (T _c =25℃)	150	1mA	200	100	15	500									102	
" 903	"	SW	Si.TMe	1500	6	7 A	50W (T _c =25℃)	150	1mA	1500	5~11.5	5	4 A		t _f < 1μS							102	ダンパ内蔵
" 904	"	"	"	1500	6	7 A	50W (T _c =25℃)	150	I _{CS} 1mA	1500	4~10	5	3 A		t _f < 1μS							102	水平偏向用
" 905	日 立	"	Si.T	1400	5	8 A	50W (T _c =25℃)	150	I _{CS} 500	1400	20	5	1 A		t _f < 1μS							102	水平偏向用
" 906	"	"	"	1400	5	8 A	50W (T _c =25℃)	150	100	1400	17	5	1 A		t _f < 1μS							102	水平偏向用
" 907																							
" 908																							
" 909																							
" 910																							
" 911	富士電機	PA	Si.TP	80	7	15A	100W (T _c =25℃)	150	100	80	120	5	2 A									102	
" 912	"	"	"	120	7	15A	100W (T _c =25℃)	150	100	120	120	5	2 A									102	
" 913	"	SW	"	200	7	25A	150W (T _c =25℃)	150	100	200	>20	5	25A		t _{on} < 1μS, t _{off} < 0.4μS							172	
" 914	"	"	"	200	7	25A	150W (T _c =25℃)	150	100	200	>20	5	25A		t _{on} < 1μS, t _{off} < 0.4μS							172	
" 915	"	"	"	600	6	30A	200W (T _c =25℃)	150	1mA	600	300	5	30A									318	
" 916	"	SW.PA	"	60	6	7 A	30W (T _c =25℃)	150	100	60	>800	1.5A	3 A									268	ターリントン
" 917	松 下	SW	"	330	6	7 A	70W (T _c =25℃)	150	15mA	330	30	4	5 A		t _{off} < 2μS, t _f < 1μS							152	
" 918	日 電	PA	Si.T	250	5	2 A	80W (T _c =25℃)	150	100	200	100	10	500									295	
" 919	松 下	AF	Si.EP	30	5	500	400	125	0.1	20	60~340	10	150					200 *	6			276	
" 920	富士電機	PA	Si.TP	200	6	5 A	100W (T _c =25℃)	150	1mA	200	>700	4	1 A	12	-500			25 *	35			102	
" 921	"	"	"	200	6	5 A	80W (T _c =25℃)	150	1mA	200	>700	4	1 A	12	-500			25 *	35			220	
" 922	"	"	"	150	6	10A	100W (T _c =25℃)	150	1mA	150	>700	4	3 A	12	-500			25 *	45			102	
" 923	"	"	"	150	6	10A	80W (T _c =25℃)	150	1mA	150	>700	4	3 A	12	-500			25 *	45			220	
" 924																							
" 925																							
" 926	日 立	AF.PA	Si.T	50		4 A	30W (T _c =25℃)	150	100	50	100	5	500									268	